

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTORNEY DOCKET NO. 035905-0118



Applicant: Igor G. KOUZNETSOV et al.

Title: TWO MASK FLOATING GATE EEPROM AND METHOD OF MAKING

Appl. No.: Unassigned

Filing Date: 02/05/2002

Examiner: Unassigned

Art Unit: Unassigned

INFORMATION DISCLOSURE STATEMENT
UNDER 37 CFR § 1.56

Commissioner for Patents
Washington, D.C. 20231

Sir:

Submitted herewith on Form PTO/SB/08B is a listing of documents known to Applicants in order to comply with Applicants' duty of disclosure pursuant to 37 CFR § 1.56. A copy of each listed document is being submitted to comply with the provisions of 37 CFR § 1.97 and § 1.98.

The submission of any document herewith, which is not a statutory bar, is not intended as an admission that such document constitutes prior art against the claims of the present application or that such document is considered material to patentability as defined in 37 CFR § 1.56(b). Applicants do not waive any rights to take any action which would be appropriate to antedate or otherwise remove as a competent reference any document which is determined to be a *prima facie* art reference against the claims of the present application.

Appl. No. Unassigned

TIMING OF THE DISCLOSURE

The listed documents are being submitted in compliance with 37 CFR §1.97(b), within three (3) months of the filing date of the application.

RELEVANCE OF EACH DOCUMENT

All of the documents are in English.

Applicants respectfully request that any listed document be considered by the Examiner and be made of record in the present application and that an initialed copy of Form PTO/SB/08B be returned in accordance with MPEP §609.

The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 C.F.R. §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 19-0741. Should no proper payment be enclosed herewith, as by a check being in the wrong amount, unsigned, post-dated, otherwise improper or informal or even entirely missing, the Commissioner is authorized to charge the unpaid amount to Deposit Account No. 19-0741.

Respectfully submitted,

February 5, 2002
Date

FOLEY & LARDNER
Customer Number: 22428

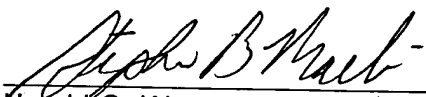


22428

PATENT TRADEMARK OFFICE

Telephone: (202) 672-5571

Facsimile: (202) 672-5399

for 
Harold C. Wegner
Attorney for Applicant
Registration No. 25,258 *Ref No 35,264*

#2/15034802
PTO/SB/08B (08-00)

Approved for use through 10/31/2002. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: February 5, 2002 <i>(use as many sheets as necessary)</i>		Complete if Known <table border="1" style="width:100%; border-collapse: collapse;"> <tr> <td style="width:50%;">Application Number</td> <td>Unassigned</td> </tr> <tr> <td>Filing Date</td> <td>02/05/2002</td> </tr> <tr> <td>First Named Inventor</td> <td>Igor KOUZNETSOV et al.</td> </tr> <tr> <td>Group Art Unit</td> <td>Unassigned</td> </tr> <tr> <td>Examiner Name</td> <td>Unassigned</td> </tr> <tr> <td>Attorney Docket Number</td> <td>035905-0118</td> </tr> </table>		Application Number	Unassigned	Filing Date	02/05/2002	First Named Inventor	Igor KOUZNETSOV et al.	Group Art Unit	Unassigned	Examiner Name	Unassigned	Attorney Docket Number	035905-0118
Application Number	Unassigned														
Filing Date	02/05/2002														
First Named Inventor	Igor KOUZNETSOV et al.														
Group Art Unit	Unassigned														
Examiner Name	Unassigned														
Attorney Docket Number	035905-0118														
Sheet	1	of	7												

10/066376
 02/05/02

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
	A1	5,427,979		Chang	06/27/1995	
	A2	5,070,384		McCollum et al.	12/03/1991	
	A3	4,498,226		Inoue et al.	02/12/1985	
	A4	4,489,478		Sakurai	12/25/1984	
	A5	4,272,880		Pashley	06/16/1981	
	A6	4,646,266		Ovshinsky et al.	02/24/1987	
	A7	5,835,396		Zhang	11/10/1998	
	A8	5,745,407		Levy et al.	04/28/1998	
	A9	5,535,156		Levy et al.	07/09/1996	
	A10	5,306,935		Esquivel et al.	04/26/1994	
	A11	4,499,557		Holmberg et al.	02/12/1985	
	A12	4,442,507		Roesner	04/10/1984	
	A13	4,507,757		McElroy	03/26/1985	
	A14	4,543,594		Mohsen et al.	09/24/1985	
	A15	4,569,121		Lim et al.	02/11/1986	
	A16	4,646,266		Ovshinsky et al.	02/24/1987	
	A17	4,820,657		Hughes et al.	04/11/1989	
	A18	4,823,181		Mohsen et al.	04/18/1989	
	A19	4,811,114		Yamamoto et al.	03/07/1989	
	A20	4,899,205		Hamdy et al.	02/06/1990	
	A21	3,863,231		Taylor	01/28/1975	
	A22	3,990,098		Mastrangelo	11/02/1976	
	A23	4,146,902		Tanimoto et al.	03/27/1979	
	A24	4,203,123		Shanks	05/13/1980	
	A25	4,203,158		Frohman-Bentchkowsky et al.	05/13/1980	
	A26	4,281,397		Neal et al.	07/28/1981	
	A27	4,419,741		Stewart et al.	12/06/1983	
	A28	4,420,766		Kasten	12/13/1983	
	A29	4,494,135		Moussie	01/15/1985	
	A30	4,922,319		Fukushima	05/01/1990	
	A31	4,943,538		Mohsen et al.	07/24/1990	
	A32	5,070,383		Sinar et al.	12/03/1991	
	A33	5,311,039		Kimura et al.	05/10/1994	
	A34	5,334,880		Abadeer et al.	08/02/1994	
	A35	5,391,907		Jang	02/21/1995	
	A36	5,441,907		Sung et al.	08/15/1995	
	A37	5,463,244		De Araujo et al.	10/31/1995	
	A38	5,536,968		Crafts et al.	07/16/1996	
	A39	5,675,547		Koga	10/07/1997	
	A40	5,737,259		Chang	04/07/1998	
	A41	5,751,012		Wolstenholme et al.	05/12/1998	
	A42	5,776,810		Guterman et al.	07/07/1998	
	A43	5,835,396		Zhang	11/10/1998	

Examiner Signature	Date Considered	
--------------------	-----------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: February 5, 2002 (use as many sheets as necessary)				Complete if Known		
				Application Number		Unassigned
				Filing Date		02/05/2002
				First Named Inventor		Igor KOUZNETSOV et al.
				Group Art Unit		Unassigned
				Examiner Name		Unassigned
Sheet <u>2</u> of <u>7</u>				Attorney Docket Number		035905-0118

U.S. PATENT DOCUMENTS					
		U.S. Patent Document			
	A44	5,883,409		Guterman et al.	03/16/1999
	A45	6,034,882		Johnson et al.	03/07/2000
	A46	3,629,863		Neale	12/21/1971
	A47	3,571,809		Nelson	03/23/1971
	A48	3,573,757		Adams	04/06/1971
	A49	3,699,543		Neale	10/17/1972
	A50	3,846,767		Cohen	11/05/1974
	A51	3,877,049		Buckley	04/08/1975
	A52	3,886,577		Buckley	05/27/1975
	A53	3,922,648		Buckley	11/25/1975
	A54	3,980,505		Buckley	09/14/1976
	A55	4,177,475		Holmberg	12/04/1979
	A56	4,677,742		Johnson	07/07/1987
	A57	3,582,908		Koo	06/01/1971
	A58	3,717,852		Abbas et al.	02/20/1973
	A59	3,787,822		Riout	01/22/1974
	A60	3,634,929		Yoshida et al.	01/18/1972
	A61	4,881,114		Mohsen et al.	11/14/1989
	A62	5,391,518		Bhushan	02/21/1995
	A63	5,675,547		Koga	10/07/1997
	A64	3,728,695		Frohman-Bentchkowsky	04/17/1973
	A65	4,876,220		Mohsen et al.	10/24/1989
	A66	3,671,948		Cassen et al.	06/20/1972
	A67	3,576,549		Hess	04/27/1971
	A68	5,978,258		Manning	11/02/1999

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY
		Office ³	Number ⁴	Kind Code ⁵ (if known)		

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
	A69	JOHN H. DOUGLAS: "The Route to 3-D Chips," High Technology, September 1983, pgs. 55-59, Vol. 3, No. 9, High Technology Publishing Corporation, Boston, MA	
	A70	M. ARIENZO et al.: "Diffusion of Arsenic in Bilayer Polycrystalline Silicon Films," J. Appl. Phys., January 1984, pgs. 365-369, Vol. 55, No. 2, American Institute of Physics	

Examiner Signature	Date Considered
--------------------	-----------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: February 5, 2002 <i>(use as many sheets as necessary)</i>		Application Number	Unassigned
		Filing Date	02/05/2002
		First Named Inventor	Igor KOUZNETSOV et al.
		Group Art Unit	Unassigned
		Examiner Name	Unassigned
Sheet	3	of	7
		Attorney Docket Number	035905-0118

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
	A71	O. BELLEZZA et al.: "A New Self-Aligned Field Oxide Cell for Multimegabit Eproms," IEDM, pgs. 579-582, IEEE	
	A72	S.D. BROTHERTON et al.: "Excimer-Laser-Annealed Poly-Si Thin-Film Transistors," IEEE Transactions on Electron Devices, February 1993, pgs. 407-413, Vol. 40, No. 2, IEEE	
	A73	P. CANDELIER et al.: "Simplified 0.35-µm Flash EEPROM Process Using High-Temperature Oxide (HTO) Deposited by LPCVD as Interpoly Dielectrics and Peripheral Transistors Gate Oxide," IEEE Electron Device Letters, July 1997, pgs. 306-308, Vol. 18, No. 7, IEEE	
	A74	MIN CAO et al.: "A High-Performance Polysilicon Thin-Film Transistor Using XeCl Excimer Laser Crystallization of Pre-Patterned Amorphous Si Films," IEEE Transactions on Electron Devices, April 1996, pgs. 561-567, Vol. 43, No. 4, IEEE	
	A75	MINO CAO et al.: "A Simple EEPROM Cell Using Twin Polysilicon Thin Film Transistors," IEEE Electron Device Letters, August 1994, pgs. 304-306, Vol. 15, No. 8, IEEE	
	A76	BOMY CHEN et al.: "Yield Improvement for a 3.5-ns BICMOS Technology in a 200-mm Manufacturing Line," IBM Technology Products, 1993, pgs.301-305, VLSITSA	
	A77	VICTOR W.C. CHAN et al.: "Three Dimensional CMOS Integrated Circuits on Large Grain Polysilicon Films," IEDM, 2000, IEEE	
	A78	BOAZ EITAN et al.: "Alternate Metal Virtual Ground (AMG) - A New Scaling Concept for Very High-Density EPROM's," IEEE Electron Device Letters, pgs. 450-452, Vol. 12, No. 8, August 1991, IEEE	
	A79	BOAZ EITAN et al.: "NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell," IEEE Electron Device Letters, pgs. 543-545, Vol. 21, No. 11, November 2000, IEEE	
	A80	BOAZ EITAN et al.: "Multilevel Flash cells and their Trade-offs," IEEE Electron Device Letters, pgs. 169-172, 1996, IEEE	
	A81	DR. HEINRICH ENDERT: "Excimer Lasers as Tools for Material Processing in Manufacturing," Technical Digest: International Electron Devices Meeting, 1985, pgs. 28-29, Washington, DC, December 1-4, 1985, Göttingen, Germany	
	A82	DOV FROHMAN-BENTCHKOWSKY: "A Fully Decoded 2048-Bit Electrically Programmable FAMOS Read-Only Memory," IEEE Journal of Solid-State Circuits, pgs. 301-306, Vol. sc-6, No. 5, October 1971	
	A83	G.K. GIUST et al.: "Laser-Processed Thin-Film Transistors Fabricated from Sputtered Amorphous-Silicon Films," IEEE Transactions on Electron Devices, pgs. 207-213, Vol. 47, No. 1, January 2000, IEEE	
	A84	G.K. GIUST et al.: "High-Performance Thin-Film Transistors Fabricated Using Excimer Laser Processing and Grain Engineering," IEEE Transactions on Electron Devices, pgs. 925-932, Vol. 45, No. 4, April 1998, IEEE	

Examiner Signature		Date Considered	
--------------------	--	-----------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: February 5, 2002 (use as many sheets as necessary)				Complete if Known	
				Application Number	Unassigned
				Filing Date	02/05/2002
				First Named Inventor	Igor KOUZNETSOV et al.
				Group Art Unit	Unassigned
				Examiner Name	Unassigned
				Attorney Docket Number	035905-0118
Sheet	4	of	7		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶	
	A85	G.K. GIUST et al.: "High-Performance Laser-Processed Polysilicon Thin-Film Transistors," IEE Electron Device Letters, pgs. 77-79, Vol. 20, No. 2, February 1999, IEEE		
	A86	C. HAYZELDEN et al.: "Silicide Formation and Silicide-Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films," J. Appl. Phys. 73(12), June 15, 1993, pgs. 8279-8289, 1993 American Institute of Physics		
	A87	FUMIHIKO HAYASHI et al.: "A Self-Aligned Split-Gate Flash EEPROM Cell with 3-D Pillar Structure," 1999 Symposium on VLSI Technology Digest of Technical Papers, pgs. 87-88, Stanford University, Stanford, CA 94305, USA		
	A88	STEPHEN C.H. HO et al.: "Thermal Stability of Nickel Silicides in Different Silicon Substrates," Department of Electrical and Electronic Engineering, pgs. 105-108, 1998, IEEE		
	A89	SUNG-HOI HUR et al.: "A Poly-Si Thin-Film Transistor EEPROM Cell with a Folded Floating Gate," IEEE Transactions on Electron Devices, pgs. 436-438, Vol. 46, No. 2, February 1999, IEEE		
	A90	J. ESQUIVEL et al. "High Density Contactless, Self Aligned EPROM Cell Array Technology," Texas Instruments (Dallas), IEDM 86, pgs. 592-595, 1986, IEEE		
	A91	R. KAZEROUNIAN et al.: Alternate Metal Virtual Ground EPROM Array Implemented in a 0.8µm Process for Very High Density Applications," IEDM 91, pgs. 311-314, 1991, IEEE		
	A92	CHANG-DONG KIM et al.: "Short-Channel Amorphous-Silicon Thin-Film Transistors," IEEE Transactions on Electron Devices, pgs. 2172-2176, Vol. 43, No. 12, December 1996, IEEE		
	A93	JOHAN H. KLOOTWIJK et al.: "Deposited Inter-Polysilicon Dielectrics for Nonvolatile Memories," IEEE Transactions on Electron Devices , pgs. 1435-1445, Vol. 46, No. 7, July 1999, IEEE		
	A94	NEC Corporation: "A Novel Cell Structure for Giga-bit EPROMs and Flash Memories Using Polysilicon Thin Film Transistors," 1992 Symposium on VLSI Technology Digest of Technical Papers, pgs. 44-45, 1992, IEEE		
	A95	WEBPAGE-JA-HUM KU et al.: "High Performance pMOSFETs With Ni(Si/sub x/Ge/sub 1-x Si/Sub 0.8/Ge/sub 0.2/ gate, IEEE Xplore Citation," VLSI Technology, 200. Digest of Technical Paper Symposium on page(s): 114-115 June 13-15 2000		
	A96	NAE-IN LEE et al.: "High-Performance EEPROM's Using N- and P-Channel Polysilicon Thin-Film Transistors with Electron Cyclotron Resonance N2O-Plasma Oxide," pgs. 15-17, IEEE Electron Device Letters, Vol. 20, No. 1, January 1999, IEEE		
	A97	JIN-WOO LEE et al.: "Improved Stability of Polysilicon Thin-Film Transistors under Self-Heating and High Endurance EEPROM Cells for Systems-On-Panel," IEEE Electron Device Letters, 1998, pgs. 265-268, IEEE		

Examiner Signature		Date Considered	
--------------------	--	-----------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: February 5, 2002 <i>(use as many sheets as necessary)</i>		Complete if Known	
		Application Number	Unassigned
		Filing Date	02/05/2002
		First Named Inventor	Igor KOUZNETSOV et al.
		Group Art Unit	Unassigned
		Examiner Name	Unassigned
		Attorney Docket Number	035905-0118

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
	A98	SEOK-WOON LEE et al.: "Pd induced lateral crystallization of Amorphous Si Thin Films," Appl. Phys. Lett. 66 (13), pgs. 1671-1673, 27 March 1995, American Institute of Physics	
	A99	K. MIYASHITA et al.: "Optimized Halo Structure for 80 nm Physical Gate CMOS Technology with Indium and Antimony Highly Angled Ion Implantation," IEDM 99-645, pgs. 27.2.1-27.2.4, 1999, IEEE	
	A100	N.D. YOUNG et al.: "The Fabrication and Characterization of EEPROM Arrays on Glass Using a Low-Temperature Poly-Si TFT Process," IEEE Transactions on Electron Devices, pgs. 1930-1936, Vol. 43, No. 11, November 1996, IEEE	
	A101	JUNG-HOON OH et al.: "A High-Endurance Low-Temperature Polysilicon Thin-Film Transistor EEPROM Cell," pgs. 304-306, IEEE Electron Device Letters, Vol. 21, No. 6, June 2000, IEEE	
	A102	WEBPAGE - M.C. POON. et al.: "Thermal Stability of Cobalt and Nickel Silicides in Amorpho Crystalline Silicon," pg. 1, IEEE Xplore, Electron Devices Meeting, 1997, Proceedings, 19 Hong Kong, 2000, IEEE	
	A103	NORIAKI SATO et al.: "A New Programmable Cell Utilizing Insulator Breakdown," IEDM, 1985 pages 639-642, IEEE	
	A104	TAKEO SHIBA et al.: "In Situ Phosphorus-Doped Polysilicon Emitter Technology for Very High-Speed, Small Emitter Bipolar Transistors," IEEE Transactions on Electron Devices, pgs. 889-897, Vol. 43, No. 6, June 1996, IEEE	
	A105	SEUNGHEON SONG et al.: "High Performance Transistors with State-of-the-Art CMOS Technologies," IEDM 99, pgs. 427-430, 1999, IEEE	
	A106	VIVEK SUBRAMANIAN et al.: "Low-Leakage Germanium-Seeded Laterally-Crystallized Single-Grain 100-nm TFT's for Vertical Integration Applications," IEEE Electron Device Letters, pgs. 341-343, Vol. 20, No. 7, July 1999, IEEE	
	A107	YOSHIHIRO TAKAO et al.: "Low-Power and High-Stability SRAM Technology Using a Laser-Recrystallized p-Channel SOI MOSFET," IEEE Transactions on Electron Devices, pgs. 2147-2152, Vol. 39, No. 9, September 1992, IEEE	
	A108	KENJI TANIGUCHI et al.: "Process Modeling and Simulation: Boundary Conditions for Point Defect-Based Impurity Diffusion Model," IEEE Transactions on Computer-Aided Design, pgs. 1177-1183, Vol. 9, No. 11, November 1990, IEEE	
	A109	HONGMEI WANG et al.: "Submicron Super TFTs for 3-D VLSI Applications," IEEE Electron Device Letters, pgs. 391-393, Vol. 21, No. 9, September 2000, IEEE	

Examiner Signature	Date Considered	
--------------------	-----------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO		Completeness if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: February 5, 2002 <i>(use as many sheets as necessary)</i>		Application Number	Unassigned
		Filing Date	02/05/2002
		First Named Inventor	Igor KOUZNETSOV et al.
		Group Art Unit	Unassigned
		Examiner Name	Unassigned
Sheet 6 of 7	Attorney Docket Number	035905-0118	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
	A110	HONGMEI WANG et al.: "Submicron Super TFTs for 3-D VLSI Applications," IEEE Electron Device Letters, Vol. 21, No. 9, pgs. 439-441, September 2000, IEEE	
	A111	HONGMEI WANG et al.: "Super Thin-Film Transistor with SOI CMOS Performance Formed by a Novel Grain Enhancement Method," IEEE Transactions on Electron Devices, pgs. 1580-1586, Vol. 47, No. 8, August 2000, IEEE	
	A112	MARVIN H. WHITE et al.: "On the Go With Sonos," Circuit & Devices, pgs. 22-31, July 2000, IEEE	
	A113	B.J. WOO et al.: "A Novel Memory Cell Using Flash Array Contactless Eprom (Face) Technology," IEDM, pgs. 90-93, 1990, IEEE	
	A114	WEBPAGE - QI XIANG et al.: "Deep sub-100 nm CMOS with Ultra Low Gate Sheet Resistance NiSi," VLSI Technology, 2000. Digest of Technical Paper Symposium on... pgs. 76-77, IEEE Xplore, June 13-15, 2000	
	A115	QI XIANG et al.: "Deep Sub-100nm CMOS with Ultra Low Gate Sheet Resistance by NiSi," IEEE, pgs. 76-77, 2000, Symposium on VLSI Technology Digest of Technical Papers	
	A116	QIUXIA XU et al.: "New Ti-SALICIDE Process Using Sb and Ge Preamorphization for Sub-0.2 μ m CMOS Technology," IEEE Transactions on Electron Devices, pgs. 2002-2009, Vol. 45, No. 9, September 1998, IEEE	
	A117	KUNIYOSHI YOSHIKAWA et al.: "An Asymmetrical Lightly Doped Source Cell for Virtual Ground High-Density EPROM's," IEEE Transactions on Electron Devices, pgs. 1046-1051, Vol. 37, No. 4, April 1990, IEEE	
	A118	VIVEK SUBRAMANIAN: "Control of Nucleation and Grain Growth in Solid-Phase Crystallized Silicon for High-Performance Thin Film Transistors," A Dissertation Submitted to the Department of Electrical Engineering and the Committee of Graduate Studies of Stanford University in Partial Fulfillment of the Requirements for the Degree of Doctor of Philosophy, June 1998	
	A119	BRIAN DIPERT: "Exotic Memories, Diverse Approaches," EDN Asia, September 2001	
	A120	JOHN R. LINDSEY et al.: "Polysilicon Thin Film Transistor for Three Dimensional Memory," The 198 th Meeting of The Electrochemical Society, Volum 2000-2	
	A121	DIETMAR GOGL et al.: "A 1-Kbit EEPROM in SIMOX Technology for High-Temperature Applications up to 250° C," IEEE Journal of Solid-State Circuits, October 2000, Vol. 35, No. 10, IEEE	
	A122	STANLEY WOLF: "Silicon Processing for the VLSI Era," Semiconductor Memory Process Integration, Volume 2	

Examiner Signature	Date Considered
--------------------	-----------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT Date Submitted: February 5, 2002 (use as many sheets as necessary)				Complete if Known	
				Application Number	Unassigned
				Filing Date	02/05/2002
				First Name of Inventor	Igor KOUZNETSOV et al.
				Group Art Unit	Unassigned
				Examiner Name	Unassigned
				Attorney Docket Number	035905-0118
Sheet	7	of	7		

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Column, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
	A123	5,383,149		Hong	01/17/1995	
	A124	5,572,046		Takemura	11/05/1996	
OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ⁶
	A125	WEB PAGE-ime.org.sg; "Tachyon and IME to Build 3D Chips for Greater Speed and Performance," Press Release, dated January 18, 2002				
	A126	ICHIRO FUJIWARA et al.: "MONOS Memory Cell Scalable to 0.1µm and Beyond," pages 117-118				

Examiner Signature		Date Considered	
--------------------	--	-----------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, D.C. 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, D.C. 20231.